

Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.7)	V_{pp}	3.5	kV
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($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	- -	MAX.	5	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	- -	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	-	MAX.	10	mA
				15	
I_H	$I_T=100mA$		MAX.	10	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	100	V/ μs
(dI/dt)c	(dV/dt)c=10V/ μs , $T_j=125$		MIN.	0.5	A/ms
t_{on}	$I_G=10mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2	μs
t_{off}				20	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=8.5A t_p=380\mu s$	$T_j=25$	1.5	V
V_{TO}	Threshold voltage	$T_j=125$	0.82	V
R_D	Dynamic resistance	$T_j=125$	57	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	μA
I_{RRM}		$T_j=125$	0.3	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	4	$\text{}/W$
$R_{th(j-a)}$	junction to ambient (AC)	120	$\text{}/W$

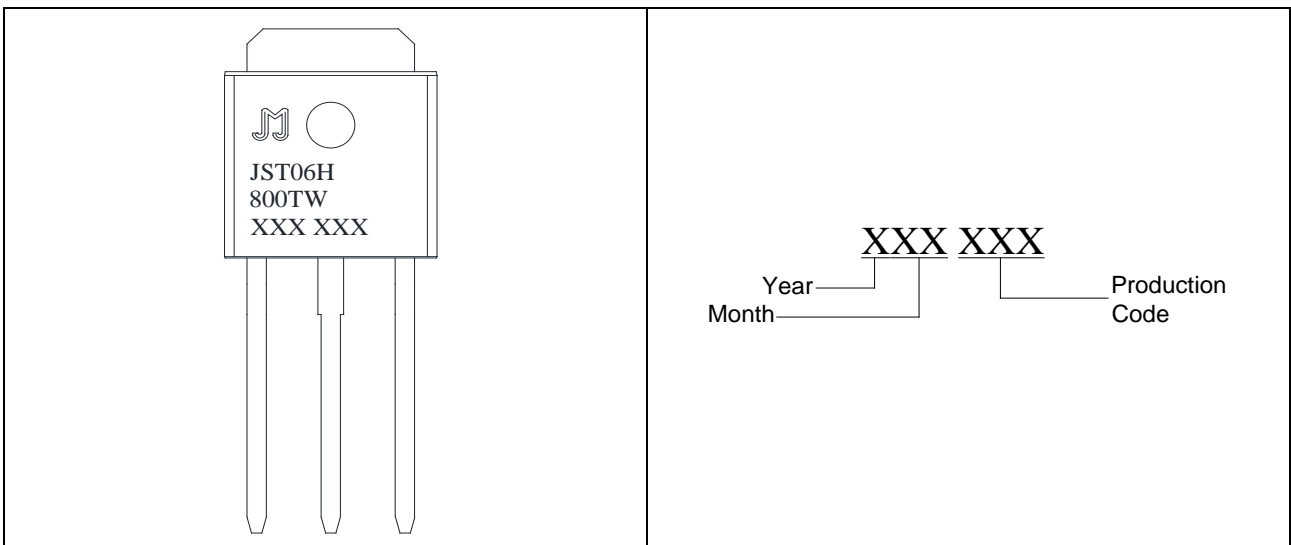
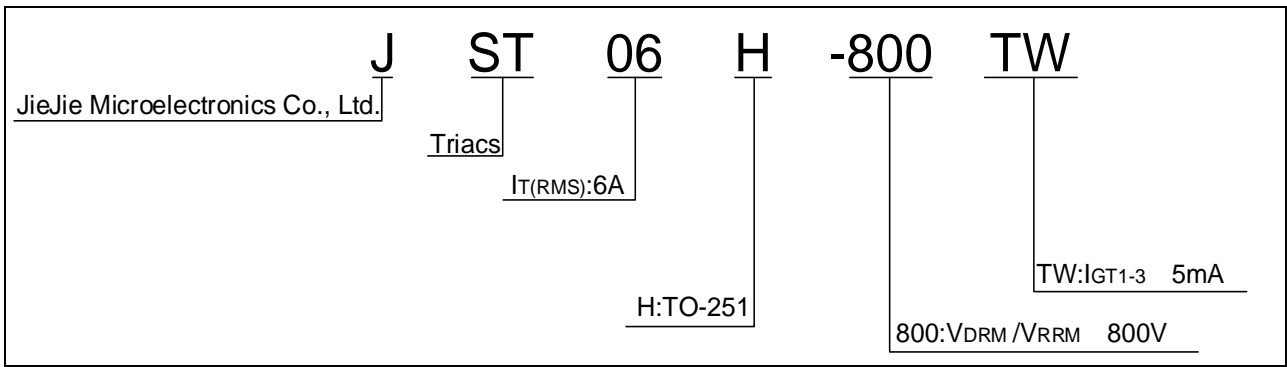


FIG.1 Maximum power dissipation versus RMS on-state current

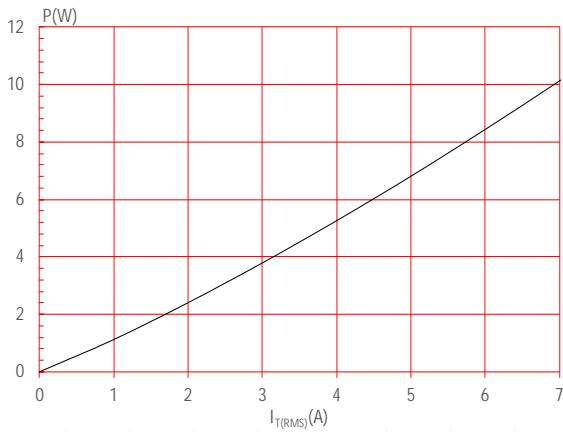


FIG.3: Surge peak on-state current versus number of cycles

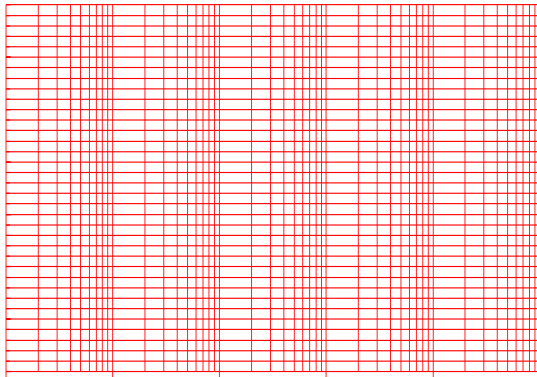


FIG.2: RMS on-state current versus case temperature

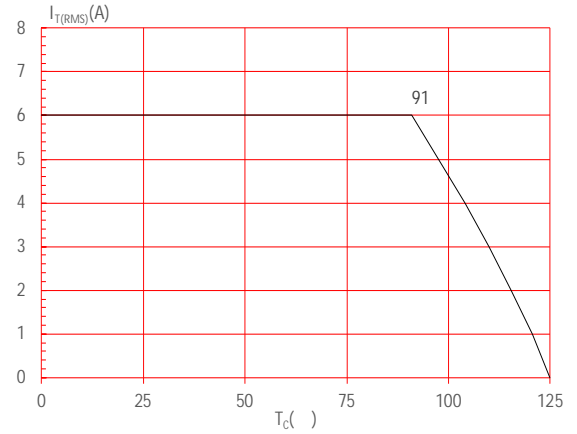
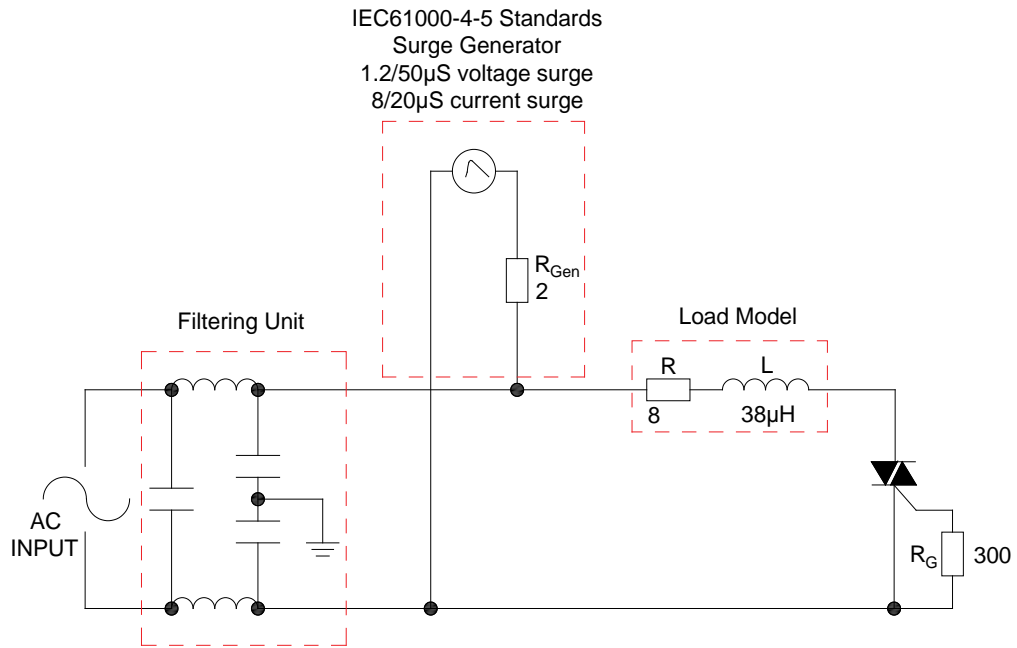


FIG.4: On-state characteristics

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards

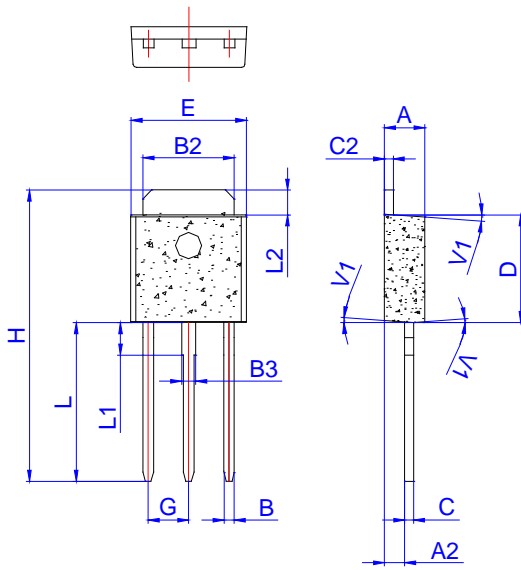


Refer to Instructions for installation of plastic-sealed in-line power devices released by JieJie

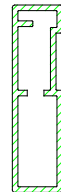
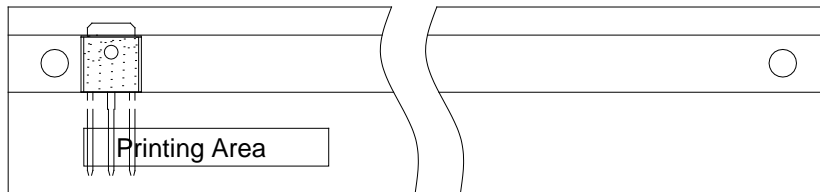
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		- -			
JST06H-800TW	800	5	TO-251	80	Tube

Document Revision History

Date	Revision	Changes
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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.20		2.40	0.086		0.095
A2	1.00		1.30	0.039		0.051
B	0.50		0.70	0.020		0.028
B2	5.10		5.40	0.200		0.213
B3	0.70		1.00	0.028		0.039
C	0.45		0.62	0.018		0.024
C2	0.48		0.62	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.70	0.252		0.264
G	2.20		2.40	0.087		0.094
H	16.0		17.0	0.630		0.669
L	8.90		9.40	0.350		0.370
L1	1.80		2.20	0.071		0.087
L2	1.25		1.55	0.049		0.061
V1		4°			4°	



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